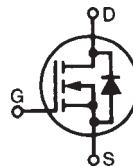


Polar™ Power MOSFET
HiPerFET™

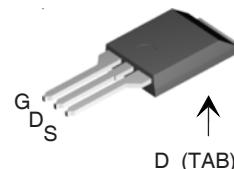
N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

IXFH15N100P
IXFV15N100P
IXFV15N100PS

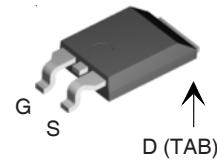


V_{DSS} = 1000V
I_{D25} = 15A
R_{DS(on)} ≤ 760mΩ
t_{rr} ≤ 300ns

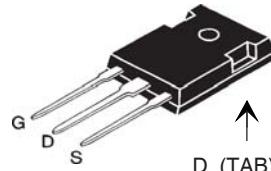
PLUS220 (IXFV)



PLUS220SMD (IXFV_S)



TO-247 (IXFH)



G = Gate D = Drain
S = Source TAB = Drain

Features

- International standard packages
- Fast recovery diode
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect

Advantages

- Easy to mount
- Space savings
- High power density

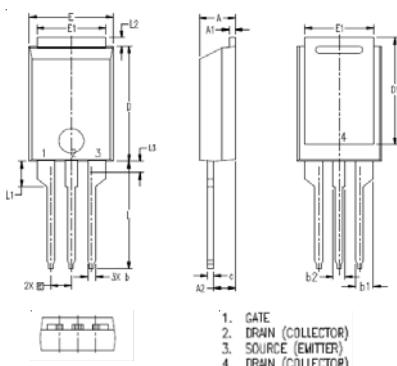
Applications:

- Switched-mode and resonant-mode power supplies
- DC-DC Converters
- Laser Drivers
- AC and DC motor controls
- Robotics and servo controls

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T _J = 25°C to 150°C	1000	V
V_{DGR}	T _J = 25°C to 150°C, R _{GS} = 1MΩ	1000	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	T _C = 25°C	15	A
I_{DM}	T _C = 25°C, pulse width limited by T _{JM}	40	A
I_{AR}	T _C = 25°C	7.5	A
E_{AS}	T _C = 25°C	500	mJ
dV/dt	I _S ≤ I _{DM} , V _{DD} ≤ V _{DSS} , T _J ≤ 150°C	15	V/ns
P_D	T _C = 25°C	543	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	Maximum lead temperature for soldering	300	°C
T_{SOLD}	Plastic body for 10s	260	°C
M_d	Mounting torque (TO-247)	1.13/10	Nm/lb.in.
F_c	Mounting force (PLUS 220)	11..65/2.5..14.6	N/lb.
Weight	TO-247 PLUS 220 types	6 4	g g

Symbol	Test Conditions (T _J = 25°C, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	V _{GS} = 0V, I _D = 1mA	1000		V
V_{GS(th)}	V _{DS} = V _{GS} , I _D = 1mA	3.5		V
I_{GS}	V _{GS} = ± 30V, V _{DS} = 0V		± 100	nA
I_{DSS}	V _{DS} = V _{DSS} V _{GS} = 0V	T _J = 125°C	25 1.0	μA mA
R_{DS(on)}	V _{GS} = 10V, I _D = 0.5 • I _{D25} , Note 1	670	760	mΩ

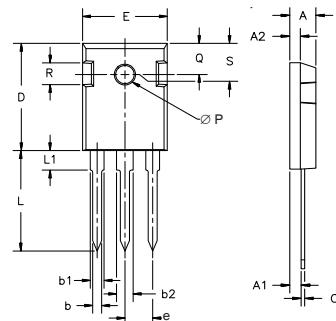
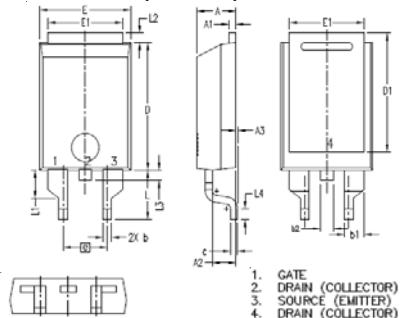
Symbol	Test Conditions (T _J = 25°C unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	V _{DS} = 20V, I _D = 0.5 • I _{D25} , Note 1	6.5	10.5	S
C_{iss}		5140		pF
C_{oss}	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz	322		pF
C_{rss}		43		pF
R_{Gi}	Gate input resistance	1.20		Ω
t_{d(on)}	Resistive Switching Times V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25} R _G = 2Ω (External)	41		ns
t_r		44		ns
t_{d(off)}		44		ns
t_f		58		ns
Q_{g(on)}	V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25}	97		nC
Q_{gs}		38		nC
Q_{gd}		42		nC
R_{thJC}			0.23 °C/W	
R_{thCS}	(TO-247, PLUS220)	0.21		°C/W

PLUS220 (IXFV) Outline

Source-Drain Diode

T_J = 25°C unless otherwise specified)

Characteristic Values		
	Min.	Typ.
		Max.
I _s	V _{GS} = 0V	15 A
I _{SM}	Repetitive	60 A
V _{SD}	I _F = I _s , V _{GS} = 0V, Note 1	1.5 V
t _{rr}	I _F = 7.5A, -di/dt = 100A/μs V _R = 100V, V _{GS} = 0V	300 ns
Q _{RM}		0.6 μC
I _{RM}		7 A

Note 1: Pulse test, t ≤ 300μs; duty cycle, d ≤ 2%.

TO-247 (IXFH) Outline

PLUS220SMD (IXFV_S) Outline


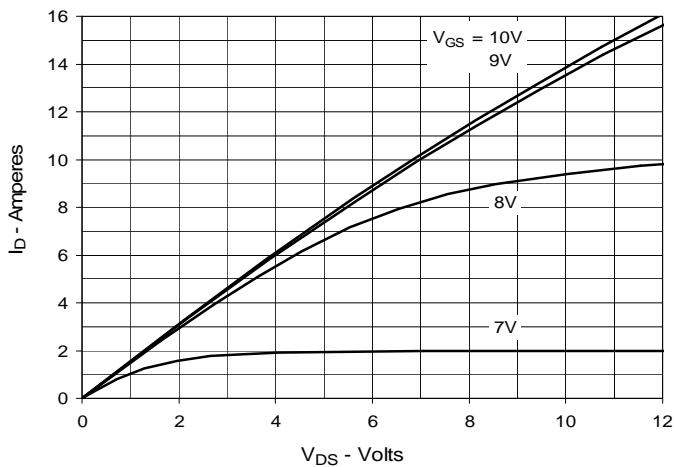
SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.169	.185	4.30	4.70
A1	.028	.035	0.70	0.90
A2	.098	.118	2.50	3.00
A3	.000	.010	0.00	0.25
b	.035	.047	0.90	1.20
b1	.080	.095	2.03	2.41
b2	.054	.064	1.37	1.63
c	.028	.035	0.70	0.90
D	.551	.591	14.00	15.00
D1	.512	.539	13.00	13.70
E	.394	.433	10.00	11.00
E1	.331	.346	8.40	8.80
e	.200BSC	.208 BSC	5.08 BSC	
L	.209	.228	5.30	5.80
L1	.118	.138	3.00	3.50
L2	.035	.051	0.90	1.30
L3	.047	.059	1.20	1.50
L4	.039	.059	1.00	1.50

IXYS reserves the right to change limits, test conditions, and dimensions.

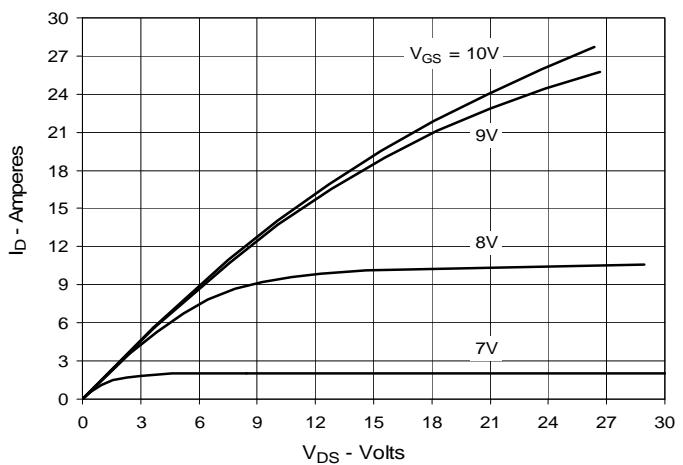
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2
4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

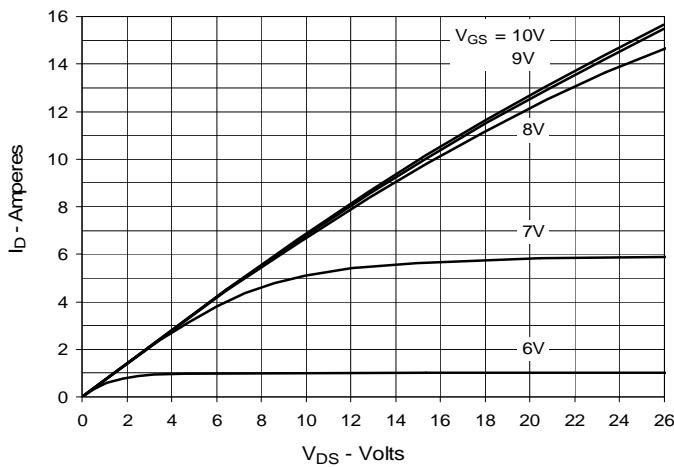
**Fig. 1. Output Characteristics
@ 25°C**



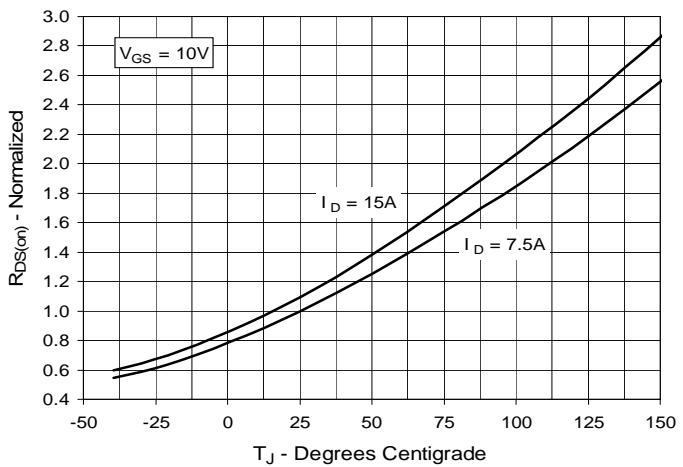
**Fig. 2. Extended Output Characteristics
@ 25°C**



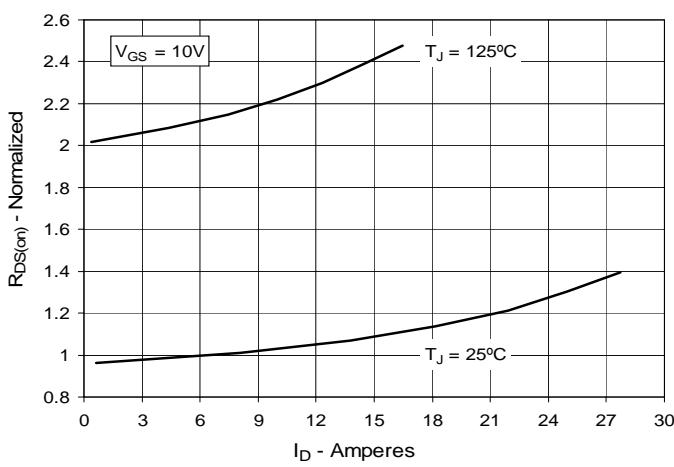
**Fig. 3. Output Characteristics
@ 125°C**



**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 7.5A$ Value
vs. Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 7.5A$ Value
vs. Drain Current**



**Fig. 6. Maximum Drain Current vs.
Case Temperature**

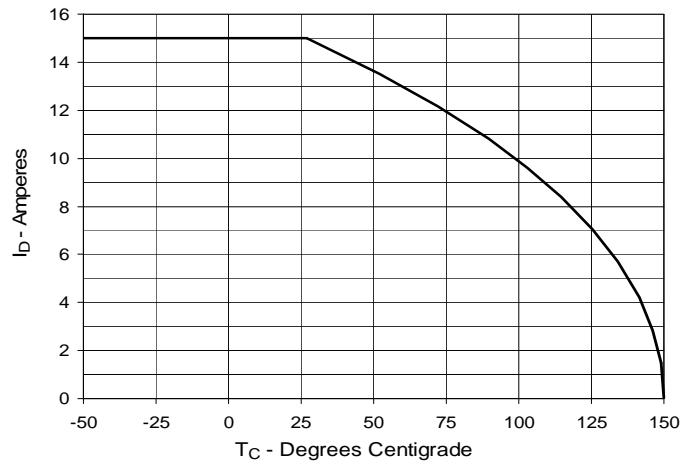
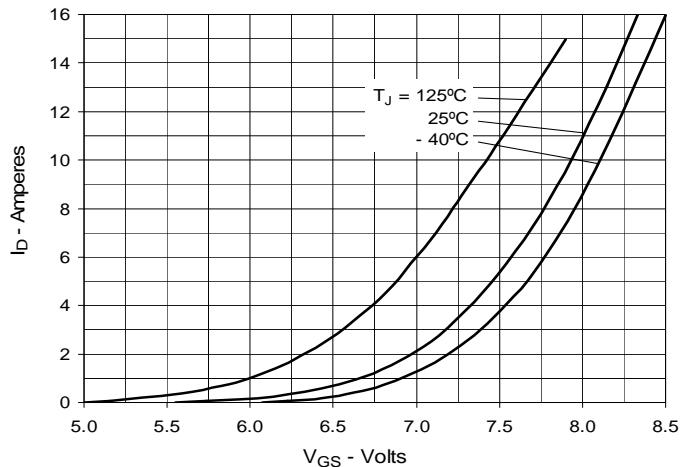
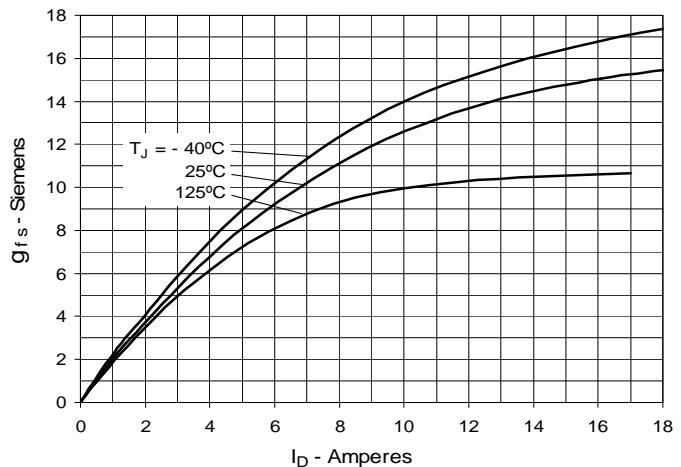
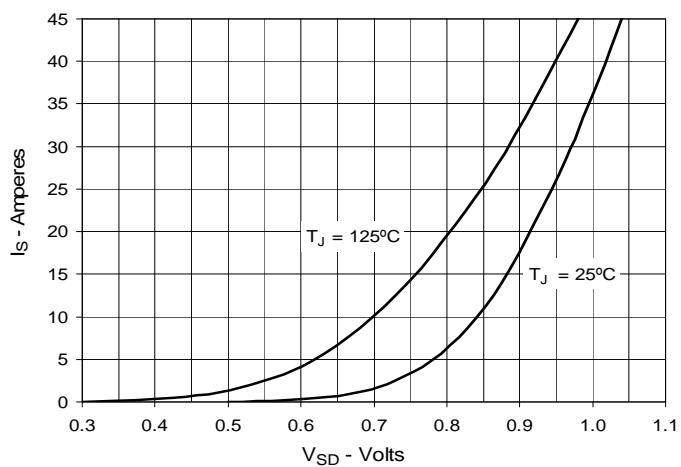
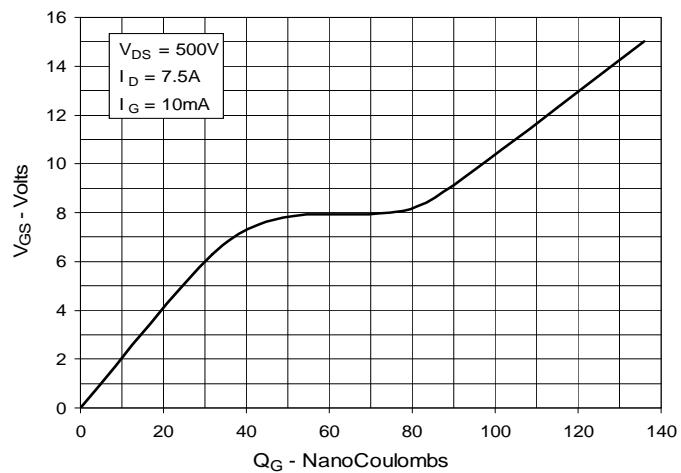
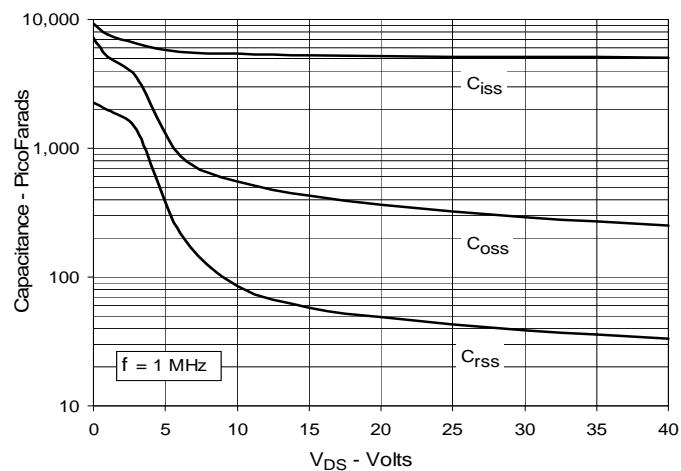
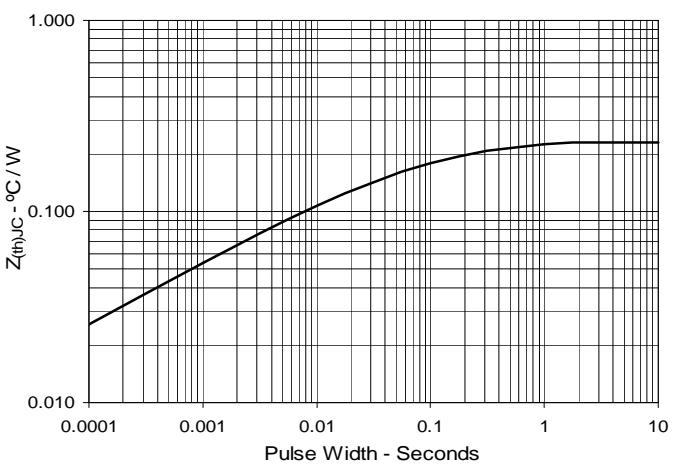


Fig. 7. Input Admittance

Fig. 8. Transconductance

Fig. 9. Forward Voltage Drop of Intrinsic Diode

Fig. 10. Gate Charge

Fig. 11. Capacitance

Fig. 12. Maximum Transient Thermal Impedance


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